



InGaAs p-i-n Photodiode

35PD500-S

The 35PD500-S, an InGaAs photodiode with a 500mm-diameter photosensitive region mounted on a metallized ceramic substrate, is a versatile device applicable to high sensitivity instrumentation, laser back-facet monitoring, and low-bit-rate telecomm and datacomm transmission. Planar semiconductor design and dielectric passivation provide for superior noise performance. Reliability is assured by a 100% purge burn-in (200°C, 15 hours, $V_r = 15V$). Chips can also be attached and wire bonded to customer-supplied or other specified packages.

Features

Planar Structure
Dielectric Passivation
100% Purge Burn-In
High Responsivity

Device Characteristics					
Parameters	Test Conditions	Min	Typ	Max	Units
Operating Voltage	-	-	-	-10	Volts
Dark Current	-5V	-	-	25	nA
Capacitance	-5V	-	20	-	pF
Responsivity	1300nm	0.80	0.9	-	A/W
	1500nm	-	1.0	-	A/W
Rise/Fall	-	-	-	3	ns
Absolute Maximum Ratings					
Reverse Voltage					15 Volts
Forward Current					50 mA
Reverse Current					5 mA
Operating Temperature					-40°C to + 85°C
Storage Temperature					-40°C to + 85°C
Soldering Temperature					250°C